



DMNH4004SPS

40V N-CHANNEL 175°C MOSFET PowerDI5060-8

Product Summary

BV _{DSS}	Rds(on)	Ι _D T _C = +25°C (Note 11)
40V	6.0mΩ @ V _{GS} = 10V	100A

Description

This MOSFET has been designed to minimize the on-state resistance $(R_{DS(ON)})$ and yet maintain superior switching performance, making it ideal for high efficiency power management applications.

Applications

- Engine Management Systems
- Body Control Electronics
- DCDC Converters

Features

- Rated to +175°C Ideal for High Ambient Temperature Environments
- 100% Unclamped Inductive Switch (UIS) Test in Production
- Low R_{DS(ON)} Minimises Power Losses
- Low Q_g Minimises Switching Losses
- <1.1mm Package Profile Ideal for Thin Applications
- Lead-Free Finish; RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)

Mechanical Data

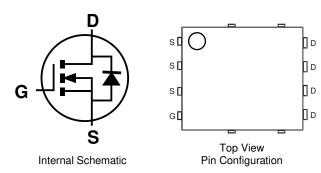
- Case: PowerDI[®]5060-8
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminal Connections: See Diagram Below
- Weight: 0.097 grams (Approximate)



Top View



Bottom View



Ordering Information (Note 4)

Part Number	Case	Packaging
DMNH4004SPS-13	PowerDI5060-8	2,500 / Tape & Reel

Notes: 1. EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant. All applicable RoHS exemptions applied. 2. See https://www.diodes.com/quality/lead-free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.

3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.</p>

4. For packaging details, go to our website at https://www.diodes.com/design/support/packaging/diodes-packaging/.

Marking Information



D: I = Manufacturer's Marking
NH4004SS = Product Type Marking Code
YYWW = Date Code Marking
YY = Last Two Digits of Year (ex: 19 = 2019)
WW = Week Code (01 to 53)

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Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit		
Drain-Source Voltage	V _{DSS}	40	V		
Gate-Source Voltage	V _{GSS}	20	V		
Continuous Drain Current (Notes 6 & 11) V_{GS} = 10V	ID	100 83	А		
Pulsed Drain Current (10µs Pulse, Duty Cycle = 1%)	I _{DM}	400	A		
Maximum Continuous Body Diode Forward Current			ls	117	A
Pulsed Source Current (10µs Pulse, Duty Cycle = 1%)			I _{SM}	400	A
Avalanche Current (Note 7) L = 1mH			I _{AS}	27	А
Avalanche Energy (Note 7) L = 1mH			Eas	536	mJ

Thermal Characteristics

Characteristic		Symbol	Value	Unit
Total Power Dissipation (Note 5)		PD	1.6	W
Thermal Resistance, Junction to Ambient (Note 5)	Steady State	$R_{\theta JA}$	96	°C/W
Total Power Dissipation (Note 6)		PD	2.8	W
Thermal Resistance, Junction to Ambient (Note 6) Steady State		$R_{ ext{ heta}JA}$	53	°C/W
Thermal Resistance, Junction to Case (Note 8)		R _{0JC}	1.2	°C/vv
Operating and Storage Temperature Range		TJ, TSTG	-55 to +175	°C

Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition	
OFF CHARACTERISTICS (Note 9)	Symbol	IVIIII	тур	IVIAX	Unit	Test condition	
Drain-Source Breakdown Voltage	BV _{DSS}	40	_	_	V	V _{GS} = 0V, I _D = 250µA	
Zero Gate Voltage Drain Current, $T_J = +25^{\circ}C$	IDSS			1	μA	$V_{\rm DS} = 0V, 10 = 200 \mu \text{A}$ $V_{\rm DS} = 32 \text{V}, V_{\rm GS} = 0 \text{V}$	
Gate-Source Leakage	-	_		±100	nA	$V_{\rm DS} = 32V, V_{\rm DS} = 0V$ $V_{\rm GS} = \pm 20V, V_{\rm DS} = 0V$	
ON CHARACTERISTICS (Note 9)	I _{GSS}			100		$V_{\rm GS} = \pm 20$ V, $V_{\rm DS} = 0$ V	
Gate Threshold Voltage	V _{GS(TH)}	2	2.5	3.5	V	$V_{DS} = V_{GS}, I_{D} = 250 \mu A$	
Static Drain-Source On-Resistance	R _{DS(ON)}	-	3.3	6	mΩ	$V_{GS} = 10V, I_D = 50A$	
Diode Forward Voltage	V _{SD}	_	0.7	1.2	V	$V_{GS} = 0V, I_S = 1.0A$	
DYNAMIC CHARACTERISTICS (Note 10)	•		•			•	
Input Capacitance	Ciss	_	2284	_	pF		
Output Capacitance	Coss	_	532	_	pF	− V _{DS} = 25V, V _{GS} = 0V, − f = 1MHz	
Reverse Transfer Capacitance	Crss	_	171	_	pF		
Gate Resistance	Rq	_	1.98	_	Ω	$V_{DS} = 0V, V_{GS} = 0V, f = 1MHz$	
Total Gate Charge (V _{GS} = 10V)	Qq	_	40	_	nC		
Gate-Source Charge	Q _{gs}	_	8.5	_	nC	V _{DS} = 32V, I _D = 86A	
Gate-Drain Charge	Q _{qd}	_	11.4	_	nC	1 .	
Turn-On Delay Time	t _{D(ON)}	_	6.3	_	ns		
Turn-On Rise Time	t _R	_	5.4	_	ns	$V_{GS} = 10V, V_{DS} = 20V,$	
Turn-Off Delay Time	tD(OFF)	_	20.5	_	ns	$R_{G} = 3.5\Omega, I_{D} = 86A$	
Turn-Off Fall Time	tF		9.0	_	ns		
Body Diode Reverse Recovery Time	t _{RR}		35.8		ns	I _F = 50A, di/dt = 100A/µs	
Body Diode Reverse Recovery Charge	Q _{RR}	_	34.7	—	nC	I _F = 50A, di/dt = 100A/µs	

Notes: 5. Device mounted on FR-4 PC board, with minimum recommended pad layout, single sided.

6. Device mounted on FR-4 substrate PC board, 2oz copper, with thermal bias to bottom layer 1 inch square copper plate.

8. Device inclusion of the substate PC board, 202 copper, with memory about a bottom $T_J = +25^{\circ}C$. 8. Thermal resistance from junction to soldering point (on the exposed drain pad). 9. Short duration pulse test used to minimize self-heating effect.

10. Guaranteed by design. Not subject to product testing.

11. Limited by package.



DMNH4004SPS

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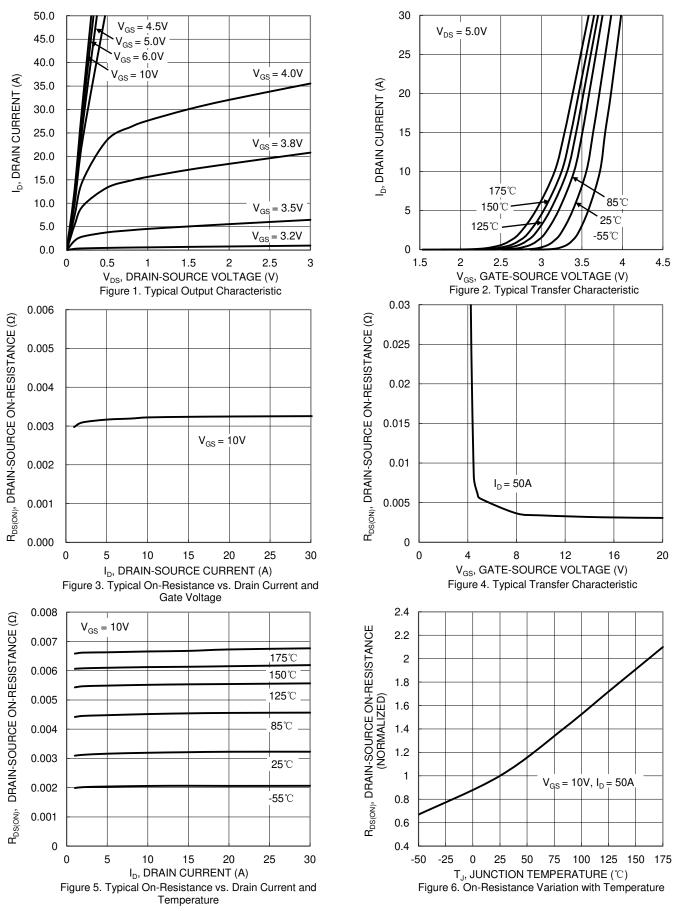
16

20

4.5

25℃

-**55°**℃





DMNH4004SPS

100 125 150 175

f = 1MHz

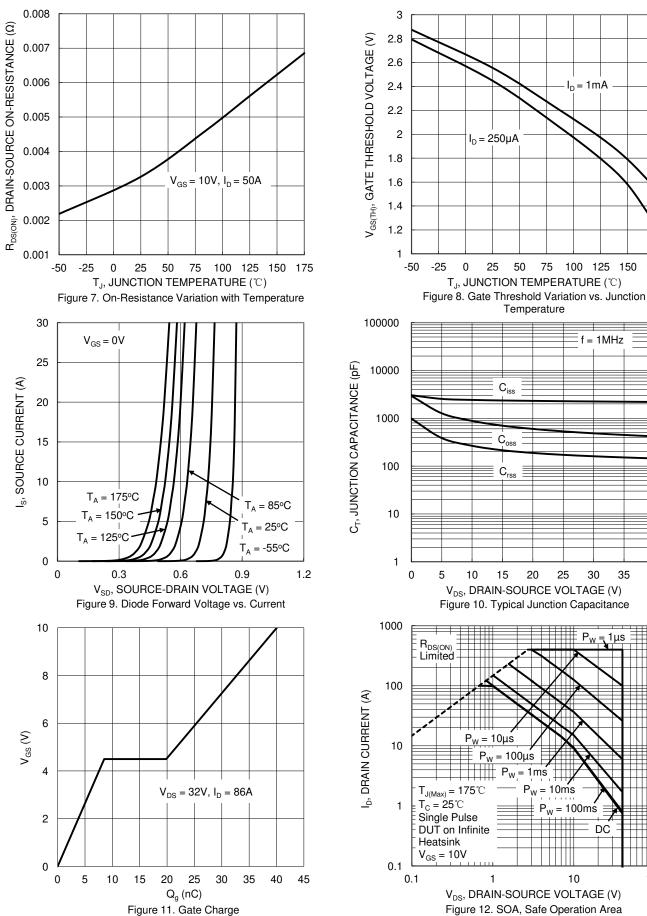
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30

35

40

 $I_D = 1mA$

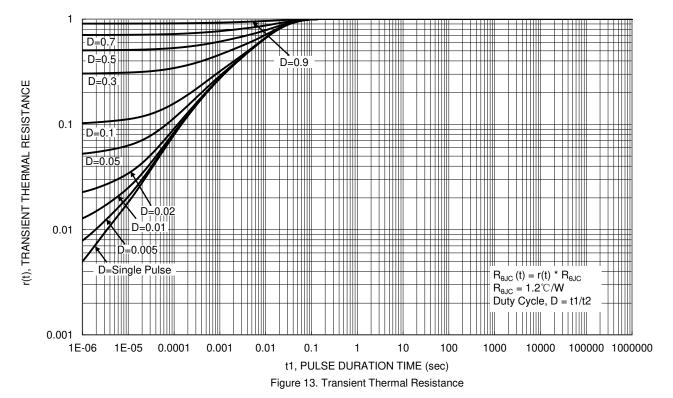


100

DC

10



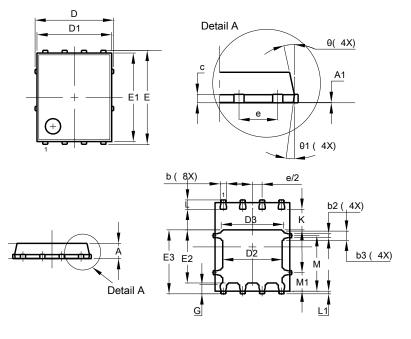




Package Outline Dimensions

Please see http://www.diodes.com/package-outlines.html for the latest version.

PowerDI5060-8

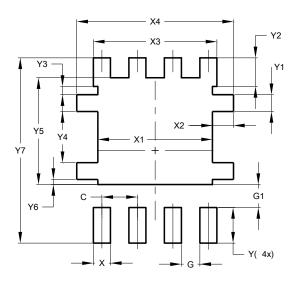


PowerDI5060-8					
Dim	Min	Max	Тур		
Α	0.90	1.10	1.00		
A1	0.00	0.05	-		
b	0.33	0.51	0.41		
b2	0.200	0.350	0.273		
b3	0.40	0.80	0.60		
c	0.230	0.330	0.277		
D		5.15 BSC			
D1	4.70	5.10	4.90		
D2	3.70	4.10	3.90		
D3	3.90	4.30	4.10		
E		6.15 BSC			
E1	5.60	6.00	5.80		
E2	3.28	3.68	3.48		
E3	3.99	4.39	4.19		
е		1.27 BSC			
G	0.51	0.71	0.61		
К	0.51	-	-		
L	0.51	0.71	0.61		
L1	0.100	0.200	0.175		
М	3.235	4.035	3.635		
M1	1.00	1.40	1.21		
Θ	10°	12°	11°		
Θ1	6°	8°	7°		
AI	All Dimensions in mm				

Suggested Pad Layout

Please see http://www.diodes.com/package-outlines.html for the latest version.

PowerDI5060-8



Dimensions	Value (in mm)
С	1.270
G	0.660
G1	0.820
X	0.610
X1	4.100
X2	0.755
X3	4.420
X4	5.610
Y	1.270
Y1	0.600
Y2	1.020
Y3	0.295
Y4	1.825
Y5	3.810
Y6	0.180
Y7	6.610



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